

ABSTRACT OF THE DISCLOSURE

In an active matrix type liquid crystal display device having a structure in which a pixel TFT is disposed in a trench carved in a substrate; with a section which is not carved in but left
5 hill-shaped being present in the vicinity of the TFT, an underneath light-shielding film 4 disposed beneath a semiconductor layer 7 of the TFT is formed so as to reach at least the top of the hill-shaped section 2a; and a metal electrode layer 9 formed above the semiconductor layer of the TFT extends to the top of the hill-shaped
10 section 2a; and besides, on the top of the hill-shaped section, a film thickness of an interlayer insulating film (5, 8) laid between the underneath light-shielding film 4 and metal electrode layer 9 is made thinner than in other sections thereof.